

General Description

The ZMC88305M combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It combines one N Channel MOSFET and one P channel MOSFET.

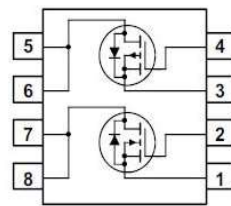
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Dual DIE in one package

Application

- Power Management in Notebook Computer
- BLDC/H-bridge Motor driver

Product Summary



$V_{DS1} = 30V$
 $V_{DS2} = -30V$
 $R_{DS(ON)1} = 22m\Omega$
 $R_{DS(ON)2} = 30m\Omega$
 $I_{D1} = 15A$
 $I_{D2} = -18A$



DFN3*3

Ordering Information:

Part NO.	ZMC88305M
Marking	88305
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	7.3	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	° C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	° C

N Channel Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	15	A
	$I_D @ T_C = 75^\circ C$	11.4	A
	$I_D @ T_C = 100^\circ C$	9.5	A

Pulsed Drain Current ^①	I_{DM}	45	A
Total Power Dissipation	$P_D@T_C=25^{\circ}C$	17	W
Total Power Dissipation	$P_D@T_A=25^{\circ}C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$
Single Pulse Avalanche Energy	E_{AS}	6	mJ

●P Channel Absolute Maximum Ratings ($T_C = 25^{\circ}C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D@T_C = 25^{\circ}C$	-18	A
	$I_D@T_C = 75^{\circ}C$	-13.5	A
	$I_D@T_C = 100^{\circ}C$	-11.3	A
Pulsed Drain Current ^①	I_{DM}	-54	A
Total Power Dissipation	$P_D@T_C=25^{\circ}C$	17	W
Total Power Dissipation	$P_D@T_A=25^{\circ}C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$
Single Pulse Avalanche Energy	E_{AS}	21	mJ

●N Channel Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2	1.6	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 6A$		22	29	$m\Omega$
		$V_{GS} = 4.5V, I_D = 4A$		30	40	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 25V, I_D = 5A$		2		S

•Dynamic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R _g	f = 1MHz		1.5		Ω
Input capacitance	C _{iss}	f = 1MHz V _{DS} =25V	-	280	-	pF
Output capacitance	C _{oss}		-	54	-	
Reverse transfer capacitance	C _{rss}		-	12	-	
Total gate charge	Q _g	V _{DD} = 15V	-	7.5	-	nC
Gate - Source charge	Q _{gs}	I _D = 6A	-	2.4	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	0.68	-	

•P Channel Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-30			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			-1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -6A		30	42	mΩ
		V _{GS} = -4.5V, I _D = -4A		44	60	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = -5A		1.5		s

•Dynamic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R _g	f = 1MHz		10		Ω
Input capacitance	C _{iss}	f = 1MHz V _{DS} = -25V	-	850	-	pF
Output capacitance	C _{oss}		-	125	-	
Reverse transfer capacitance	C _{rss}		-	115	-	
Total gate charge	Q _g	V _{DD} = -15V	-	12	-	nC
Gate - Source charge	Q _{gs}	I _D = -6A	-	5	-	
Gate - Drain charge	Q _{gd}	V _{GS} = -10V	-	6	-	

•N Channel characteristics curve

Fig.1 Power Dissipation

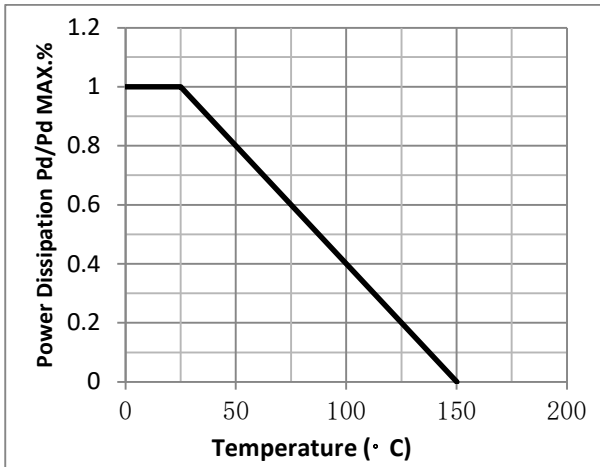


Fig.2 Typical output Characteristics

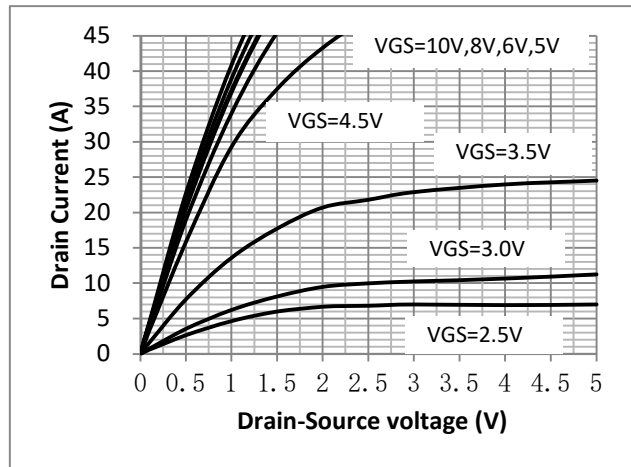


Fig.3 Threshold Voltage V.S Junction Temperature

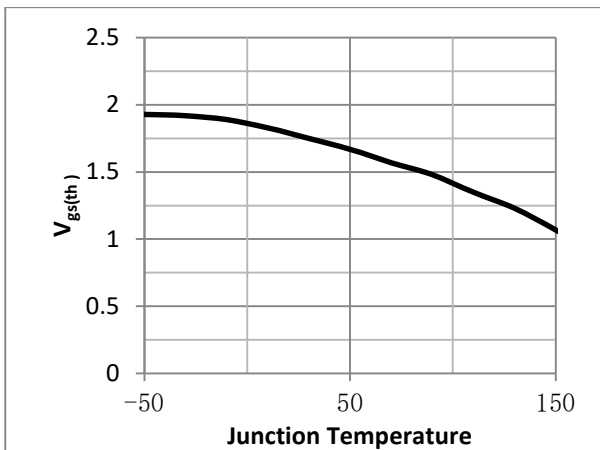


Fig.4 Resistance V.S Drain Current

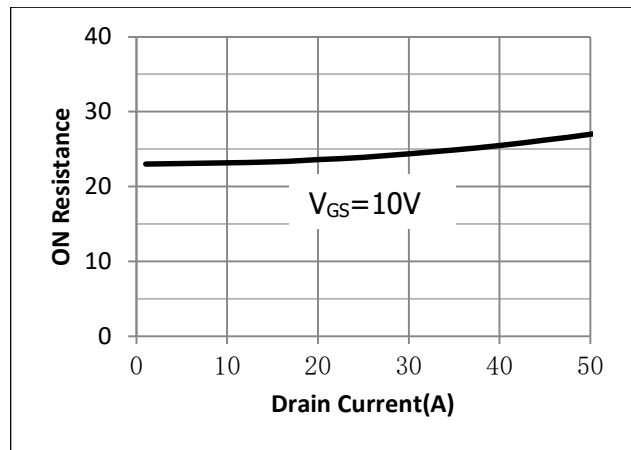


Fig.5 On-Resistance VS Gate Source Voltage

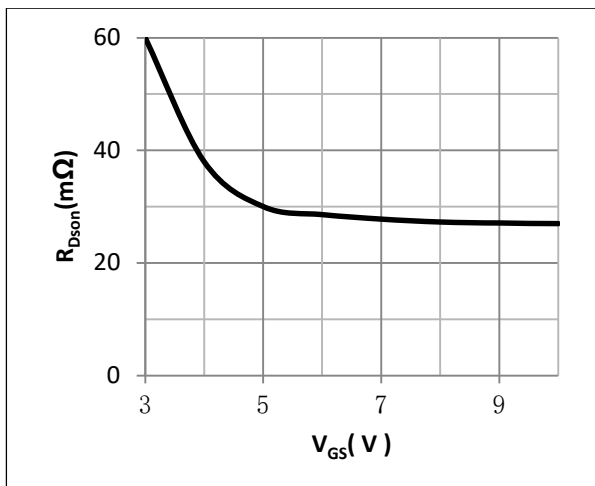
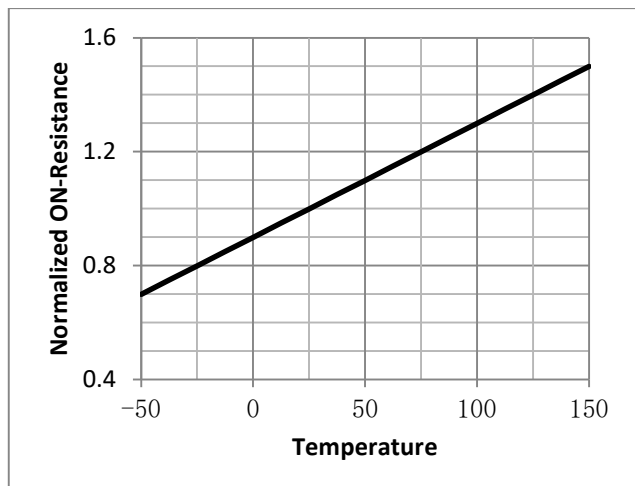


Fig.6 On-Resistance V.S Junction Temperature



•P Channel characteristics curve

Fig.1 Power Dissipation Derating Curve

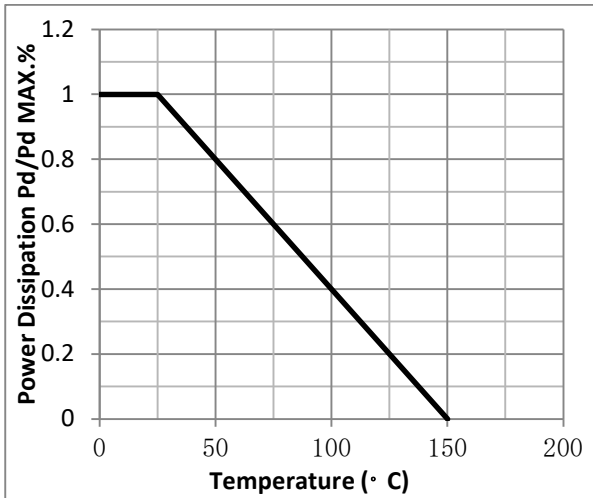


Fig.2 Typical output Characteristics

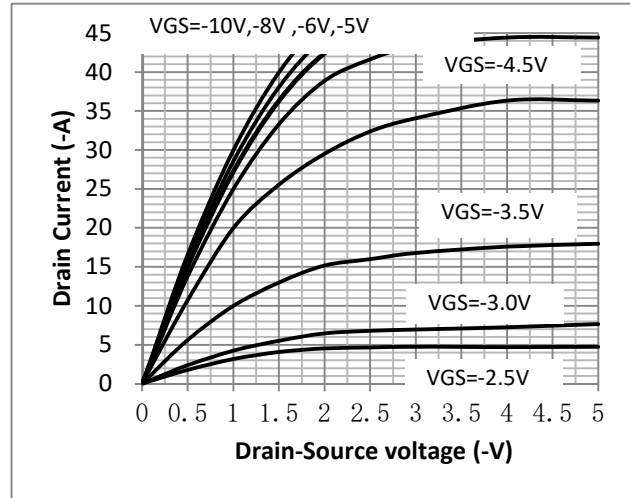


Fig.3 Threshold Voltage V.S Junction Temperature

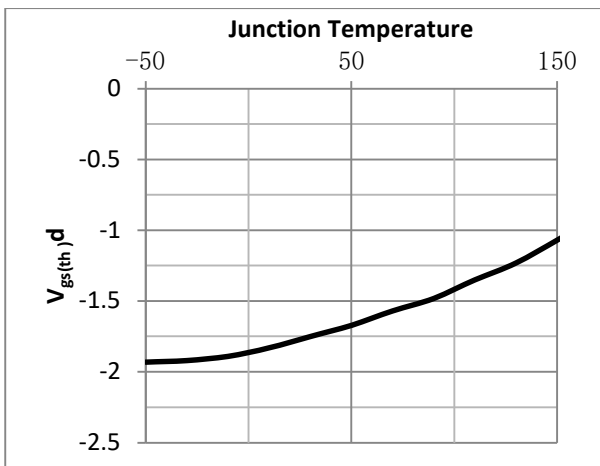


Fig.4 Resistance V.S Drain Current

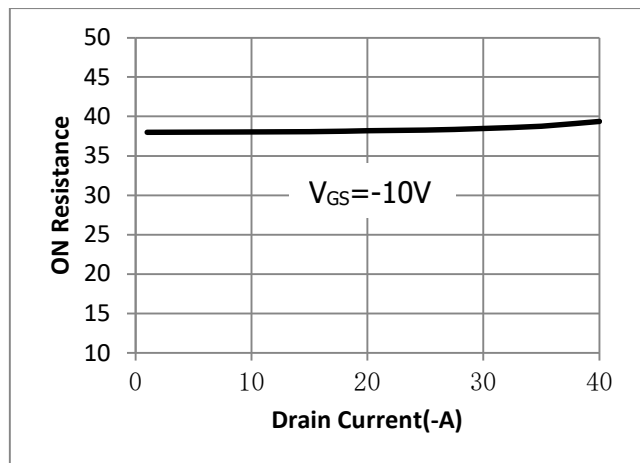


Fig.5 On-Resistance VS Gate Source Voltage

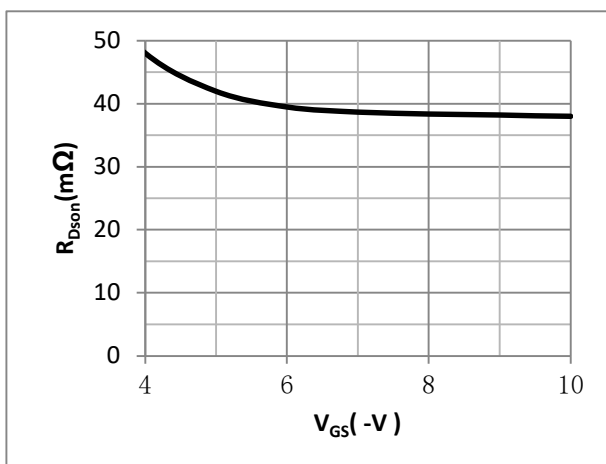
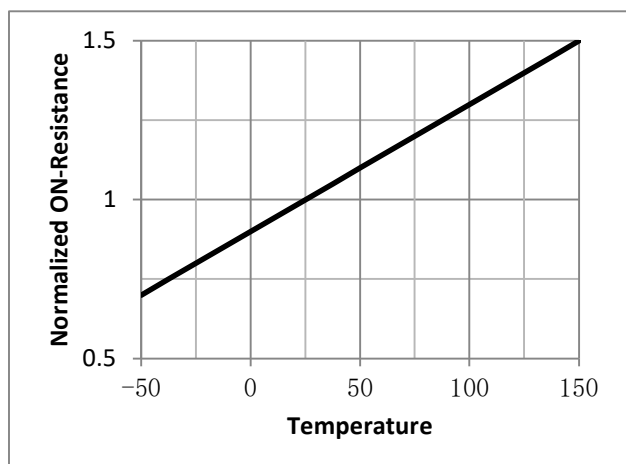


Fig.6 On-Resistance V.S Junction Temperature



•Test Circuit

Fig.1 Gate Charge Measurement Circuit

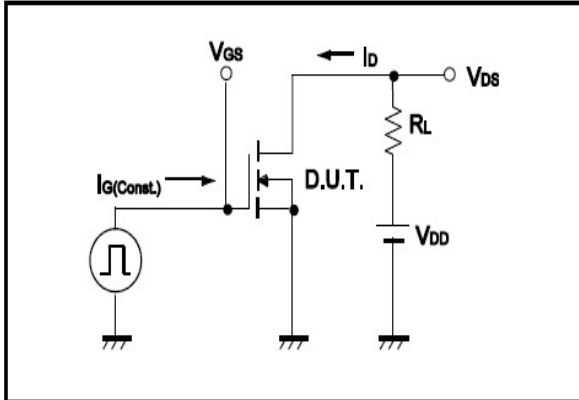


Fig.2 Gate Charge Waveform

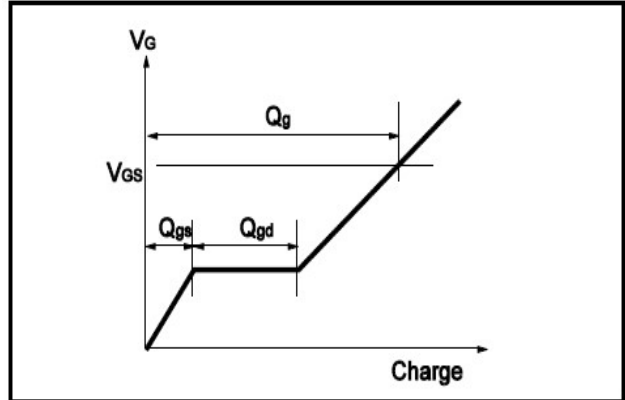


Fig.3 Switching Time Measurement Circuit

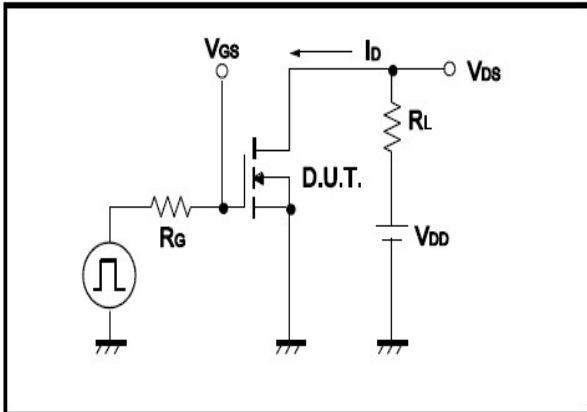


Fig.4 Switching Time Waveform

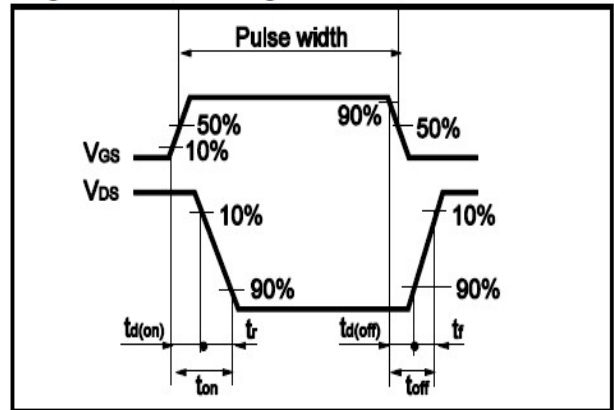


Fig.5 Avalanche Measurement Circuit

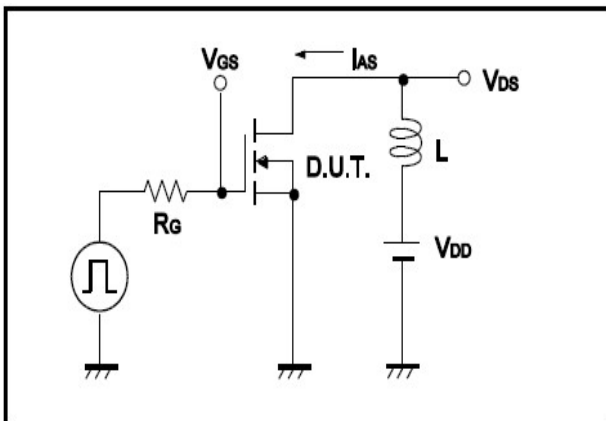
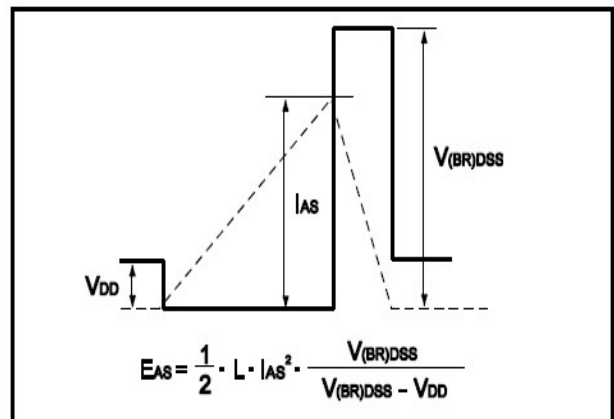
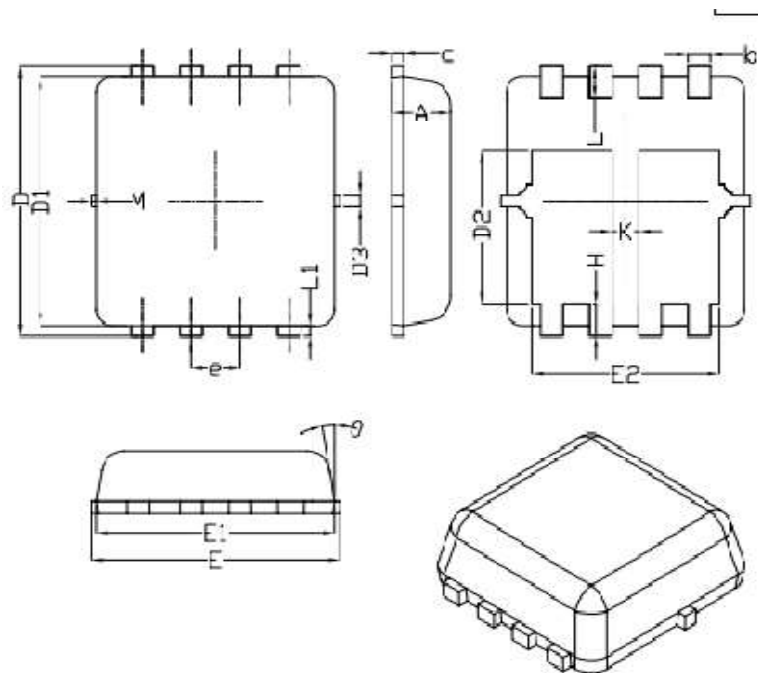


Fig.6 Avalanche Waveform



•Dimensions (DFN3×3)

Unit: mm



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
K	0.30	---	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			